

**Amendment**

Inventor: Roman J. Hamerski et al.  
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22. (New) The device of claim 2 wherein the etched first surface of the substrate forms a well that receives the diffused layer, wherein the diffused layer in the well reduces an area of the relatively high resistivity material in the substrate to reduce a resulting electric field.
23. (New) The device of claim 8 wherein the etched second surface of the epitaxial layer of relatively high resistivity material forms a well that reduces an area of the relatively high resistivity material in the second surface of the epitaxial layer of relatively high resistivity material to reduce a resulting electric field.
24. (New) The device of claim 15 wherein the second surface of the epitaxial layer of relatively high resistivity material receives a lesser amount of diffused material to form a well that reduces an area of the relatively high resistivity material in the second surface of the epitaxial layer of relatively high resistivity material to reduce a resulting electric field.
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